Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (canceled).

Claim 2 (currently amended). ~~The shielding device according to claim 1, wherein:~~ A semiconductor chip, comprising

a SOI substrate having an integrated circuit ~~said substrate is an SOI substrate~~; and

a shielding device for said integrated circuit, said shielding device having a shield disposed on a side of said integrated circuit in the semiconductor chip facing said SOI substrate, said shield at least one of optically and electrically shielding said integrated circuit, said shield ~~is~~ being an insulation layer of said SOI substrate.

Claim 3 (canceled).

Claim 4 (currently amended). ~~The shielding device according to claim 3, wherein:~~ A semiconductor chip, comprising

a SOI substrate having an integrated circuit, said ~~the substrate is an~~ SOI substrate having:

a bulk silicon layer;

a body silicon layer having at least one component formed therein; and

an insulator layer having a via, said insulator layer disposed between said bulk silicon layer and said body silicon layer;

a shielding device for said integrated circuit, said shielding device having a shield disposed on a side of said integrated circuit in the semiconductor chip facing said SOI substrate, said shield at least one of optically and electrically shielding said integrated circuit, said shield being at least one conductor disposed in said SOI substrate on said side of said integrated circuit facing said SOI substrate, said conductor ~~is~~ disposed in said bulk silicon layer; and

said via electrically ~~connects~~ connecting said conductor to at least one of said body silicon layer and said component.

Claim 5 (currently amended). The shielding device according to claim 4 ~~3~~, wherein said conductor is an element selected

from the group consisting of a conductor surface, a conductor track, a conductor grid and a conductor double grid.

Claim 6 (currently amended). ~~The shielding device according to claim 3, wherein~~ A semiconductor chip, comprising

a substrate having an integrated circuit; and

a shielding device for said integrated circuit, said shielding device having a shield disposed on a side of said integrated circuit in the semiconductor chip facing said substrate, said shield at least one of optically and electrically shielding said integrated circuit, said shield being at least one conductor disposed in said substrate on said side of said integrated circuit facing said substrate, said conductor ~~is~~ being a doped region in ~~the~~ said substrate.

Claim 7 (canceled).

Claim 8 (currently amended). ~~The shielding device according to claim 7, wherein:~~ A semiconductor chip, comprising:

a SOI substrate having an integrated circuit ~~said substrate is an SOI substrate~~; and

a shielding device for said integrated circuit, said shielding device having shielding means for at least one of optical and electrical shielding said integrated circuit and disposed on a side of said integrated circuit in the semiconductor chip facing said SOI substrate, said shielding means ~~is~~ being an insulation layer of said SOI substrate.

Claim 9 (canceled).

Claim 10 (currently amended). ~~The shielding device according to claim 9, wherein:~~ A semiconductor chip, comprising:

a SOI substrate having an integrated circuit, said ~~the substrate is an~~ SOI substrate having:

a bulk silicon layer;

a body silicon layer having at least one component formed therein; and

an insulator layer having a via, said insulator layer disposed between said bulk silicon layer and said body silicon layer;

a shielding device for said integrated circuit, said shielding device having shielding means for at least one of optical and

electrical shielding said integrated circuit and disposed on a side of said integrated circuit in the semiconductor chip facing said SOI substrate, said shielding means is at least one conductor disposed in said SOI substrate on said side of said integrated circuit facing said SOI substrate, said conductor ~~is~~ disposed in said bulk silicon layer; and

said via electrically ~~connects~~ connecting said conductor to at least one of said body silicon layer and said component.

Claim 11 (currently amended). The shielding device according to claim 10 ~~9~~, wherein said conductor is an element selected from the group consisting of a conductor surface, a conductor track, a conductor grid and a conductor double grid.

Claim 12 (currently amended). ~~The shielding device according to claim 9, wherein~~ A semiconductor chip, comprising:

a substrate having an integrated circuit; and

a shielding device for said integrated circuit, said shielding device having shielding means for at least one of optical and electrical shielding said integrated circuit and disposed on a side of said integrated circuit in the semiconductor chip facing said substrate, said shielding means is at least one conductor disposed in said substrate on said side of said

integrated circuit facing said substrate, said conductor ~~is~~ being a doped region in ~~the~~ said substrate